

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	1.6 1.2	А
	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	2.0 1.6	А
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	2.3 1.8	А
	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	2.9 2.3	А
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	1.5	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	10	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Bower Dissination (Note 5)	T _A = +25°C	ס	0.7	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	P_{D}	0.4		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	J	183	°C/W	
	t<10s	$R_{\theta JA}$	115	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	D-	1.3	W	
Total Fower Dissipation (Note 0)	$T_A = +70^{\circ}C$	P_D	0.8	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	J	94	°C/W	
	t<10s	$R_{\theta JA}$	61		
Thermal Resistance, Junction to Case		$R_{ hetaJC}$	39		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

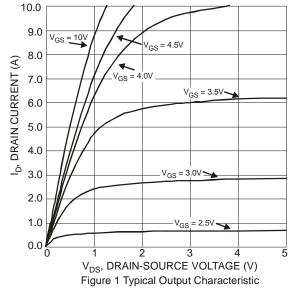
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

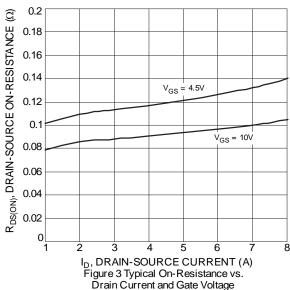
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			92	140	mΩ	$V_{GS} = 10V, I_D = 1.8A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	1	115	170		$V_{GS} = 4.5V, I_D = 1.3A$	
Forward Transfer Admittance	Y _{fs}		2.2	_	S	$V_{DS} = 15V, I_{D} = 1.8A$	
Diode Forward Voltage	V_{SD}	_	0.75	1.0	V	$V_{GS} = 0V, I_S = 0.45A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	1	315			V _{DS} = 40V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss	l	18	l	pF		
Reverse Transfer Capacitance	Crss		16	_			
Gate Resistnace	R_g	_	0.65	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_g		8.6	_		V _{DS} = 30V, I _D = 1.8A	
Total Gate Charge (V _{GS} = 5V)	Qg	_	4.1	_	nC		
Gate-Source Charge	Q_{gs}	_	1.0	_	IIC		
Gate-Drain Charge	Q_{gd}	_	1.7	_			
Turn-On Delay Time	t _{D(on)}	_	2.6	_		$V_{DS} = 30V, V_{GS} = 10V,$ $R_{G} = 6.0\Omega, I_{D} = 1.8A$	
Turn-On Rise Time	t _r	_	3.6	_	20		
Turn-Off Delay Time	t _{D(off)}		16.3	_	ns		
Turn-Off Fall Time	t _f	_	2.7	_			
Reverse Recovery Time	t _{rr}		16.8	_	ns ,		
Reverse Recovery Charge	Qrr		9.0	_	nC	$_{\rm nC}$ I _F = 1.8A, di/dt =100A/µs	

Notes

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1in. square copper plate.
- 7 .Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







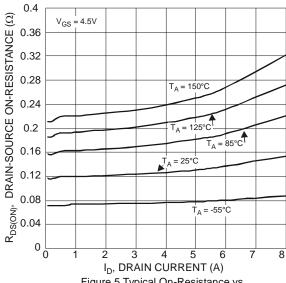
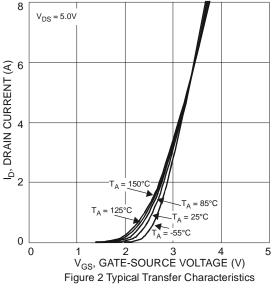
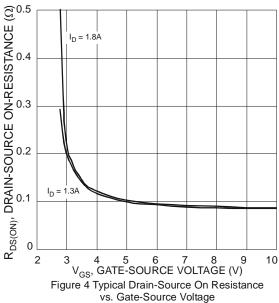
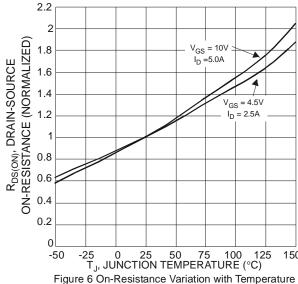


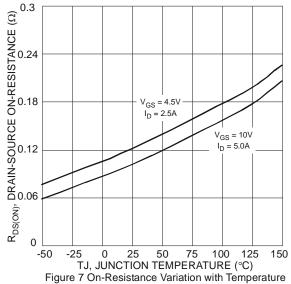
Figure 5 Typical On-Resistance vs. Drain Current and Temperature

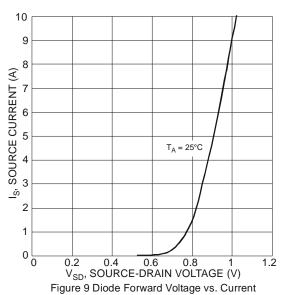


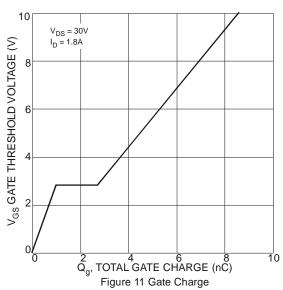












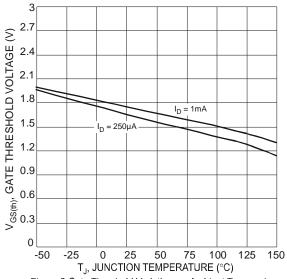
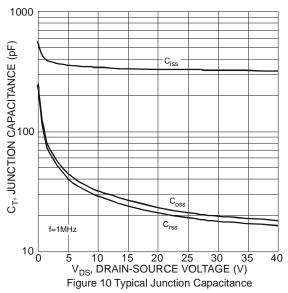
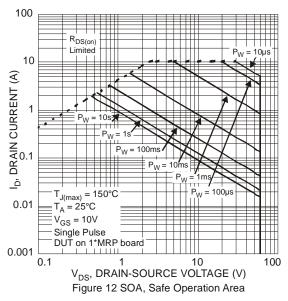
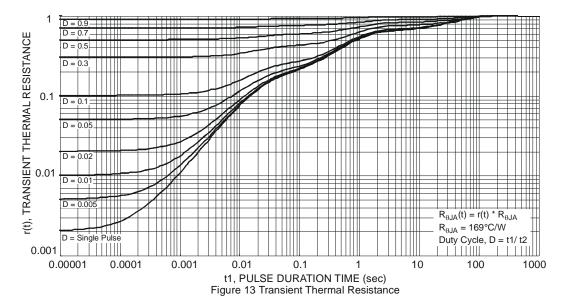


Figure 8 Gate Threshold Variation vs. Ambient Temperature



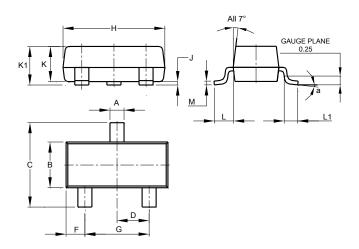






Package Outline Dimensions

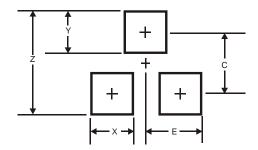
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
C	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Η	2.80	3.00	2.90		
7	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
٦	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
α	α 8°				
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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